

1-Line Ultra Small Bi-directional TVS Diode

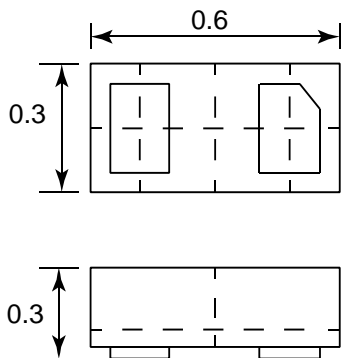
Description

The PESDU3311P0T is a bi-directional TVS diode, to provide fast-response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data. The PESDU3311P0T complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free DFN package. The ultra-small size and high ESD protection make PESDU3311P0T an ideal choice to replace 0201 size multilayer varistors (MLVs) and protect cell phone, digital cameras, audio players and many other portable applications.

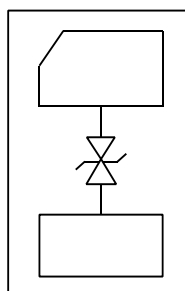
Features

- Ultra small package: 0.6x0.3x0.3mm
- Protects one data or power line
- Operating voltage: 3.3V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 30\text{kV}$
Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 7.5A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

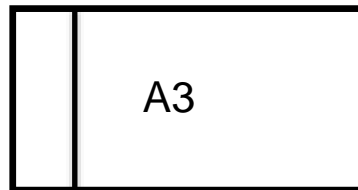
Mechanical Characteristics

- Package: DFN0603-2 (0.6x0.3x0.3mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



A3= Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU3311P0T	10000/Tape & Reel	7 inch

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	75	W
Peak Pulse Current (8/20μs)	I _{PP}	7.5	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Lead temperature	T _L	260	°C
Operating Temperature Range	T _{OP}	-40 ~ +85	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Breakdown Voltage	V _{BR}	3.8			V	I _T = 1mA
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 3.3V
Clamping voltage ¹⁾	V _{CL}		8		V	I _{PP} = 16A, t _p = 100ns
Dynamic resistance ¹⁾	R _{DYN}		0.25		Ω	
Clamping Voltage ²⁾	V _C		8		V	V _{ESD} = 8kV
Clamping Voltage ³⁾	V _C		5.5	7	V	I _{PP} = 1A, t _p = 8/20μs
Clamping Voltage ³⁾	V _C		8	10	V	I _{PP} = 7.5A, t _p = 8/20μs
Junction Capacitance	C _J		13	20	pF	V _R = 0V, f = 1MHz

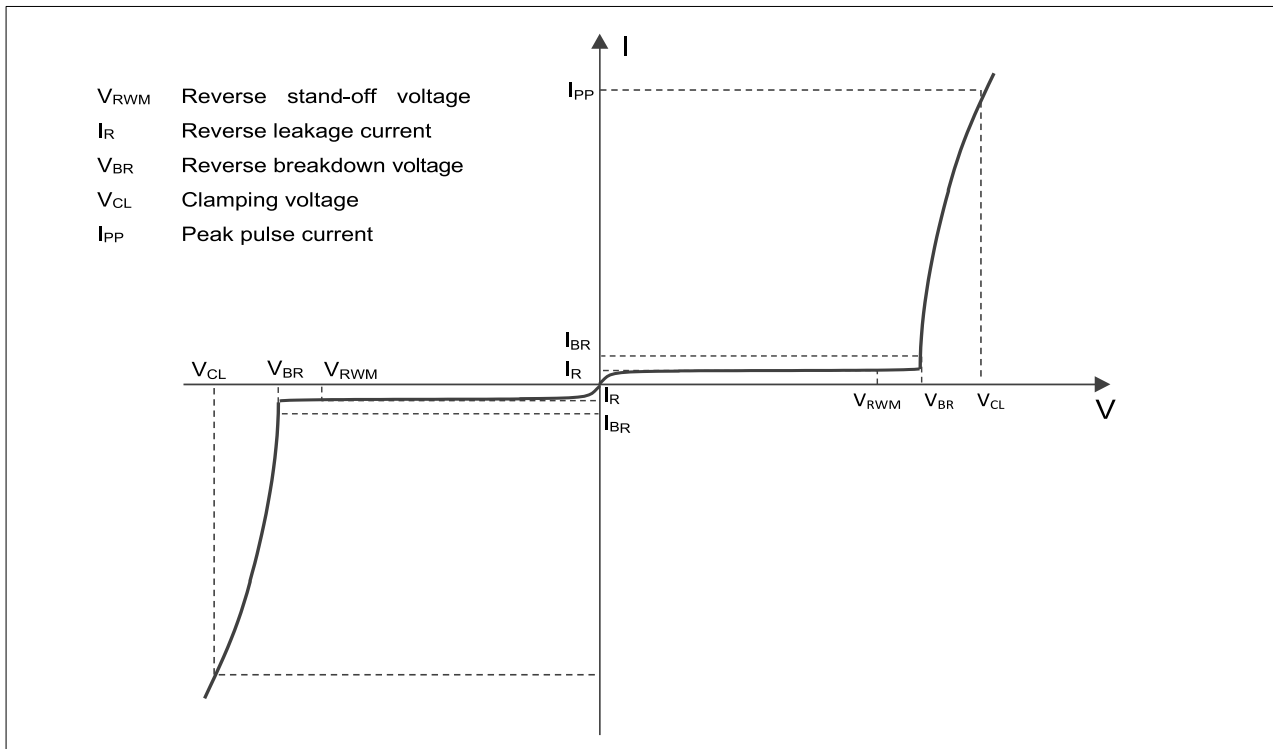
Notes:

1) TLP parameter: Z₀ = 50Ω, t_p = 100ns, t_r = 2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

2) Contact discharge mode, according to IEC61000-4-2.

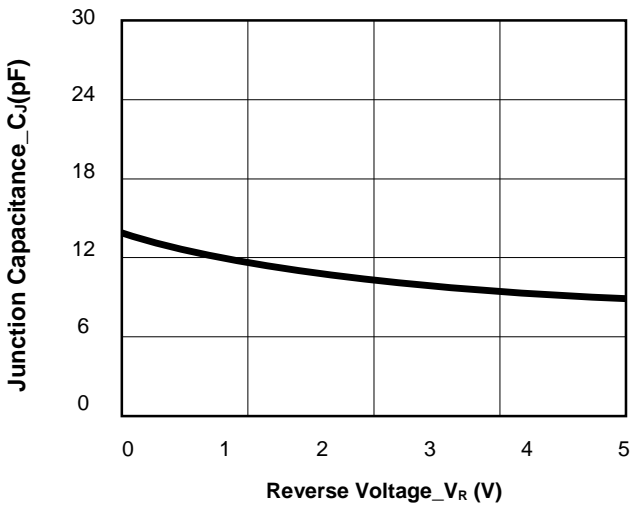
3) Non-repetitive current pulse, according to IEC61000-4-5.

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

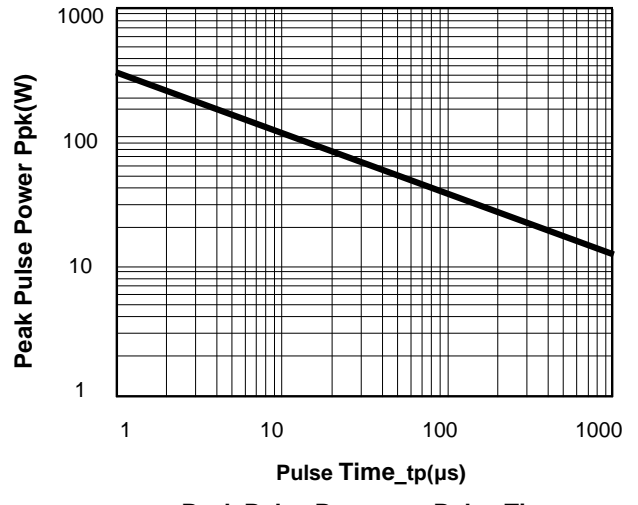


Definitions of electrical characteristics

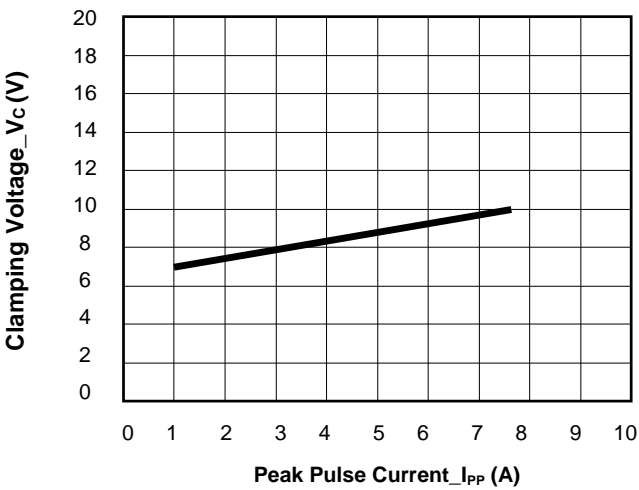
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



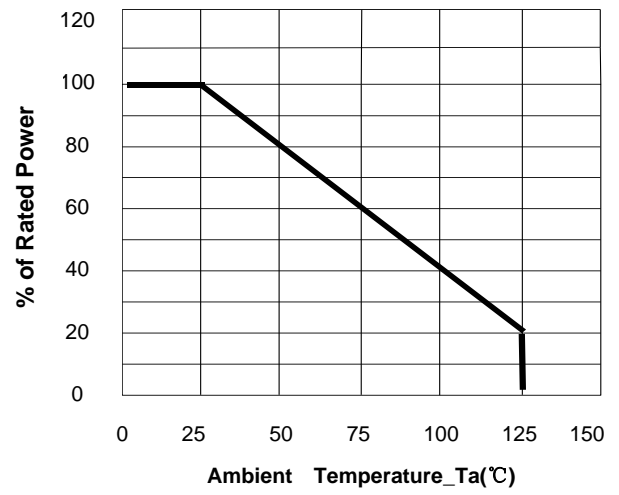
Junction Capacitance vs. Reverse Voltage



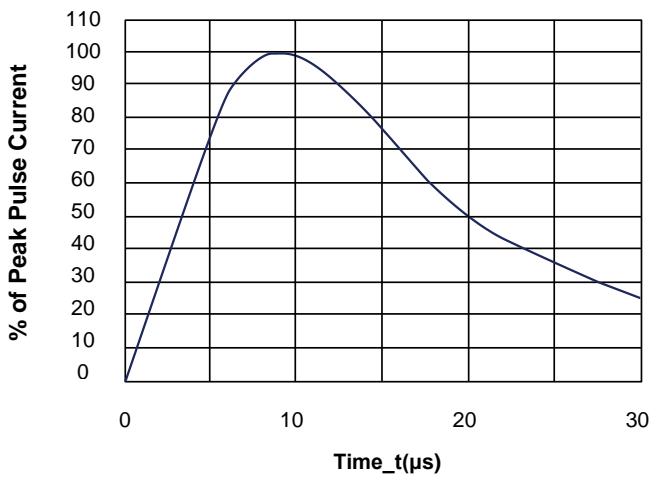
Peak Pulse Power vs. Pulse Time



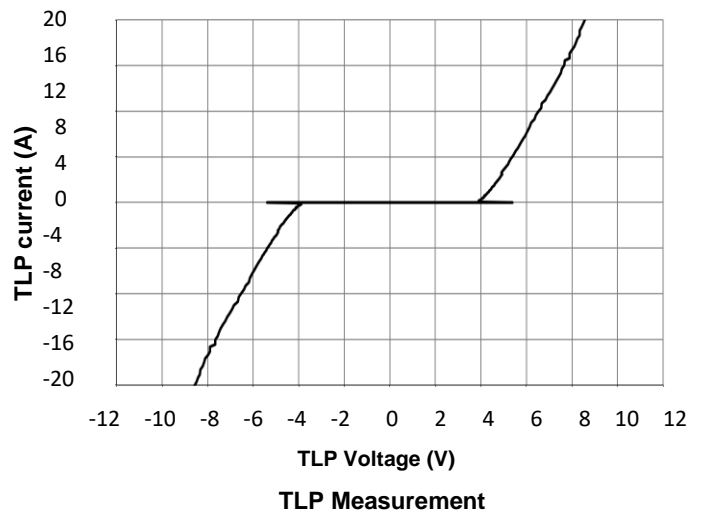
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

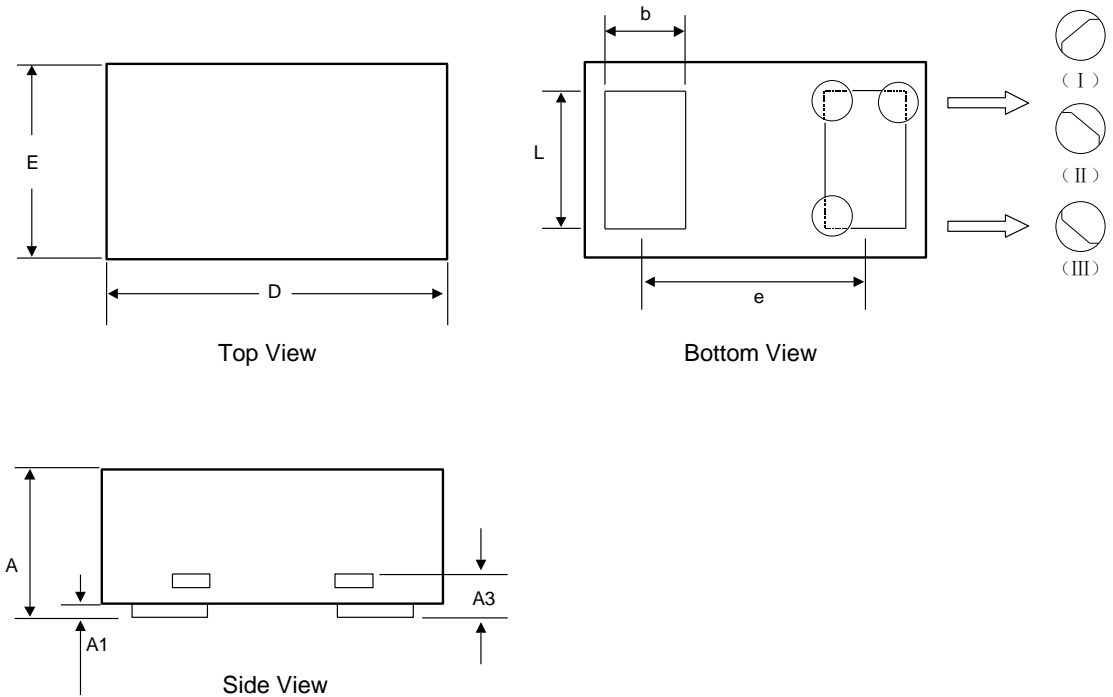


8/20μs Pulse Waveform



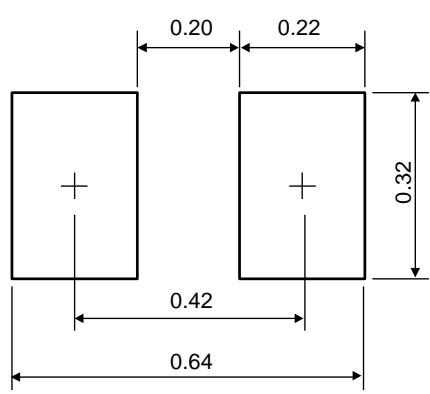
TLP Measurement

DFN0603-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.230	0.300	0.350
A1	0.000	-	0.050
A3	0.102REF.		
D	0.550	0.600	0.670
E	0.250	0.300	0.370
b	0.160	0.190	0.230
L	0.215	0.245	0.275
e	0.360 BSC		

Recommended PCB Layout (Unit: mm)

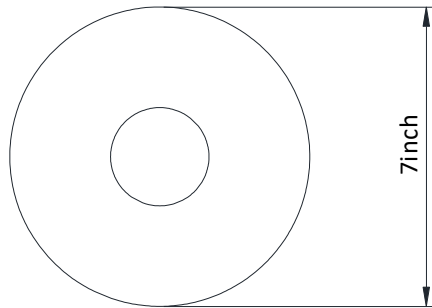


Notes:

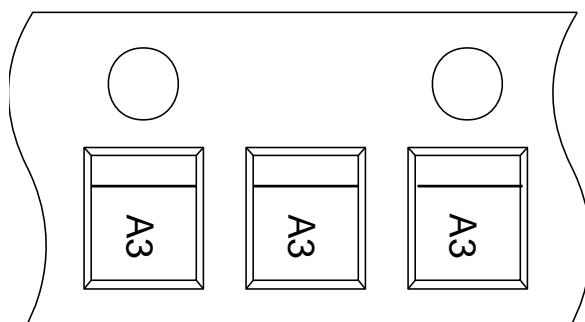
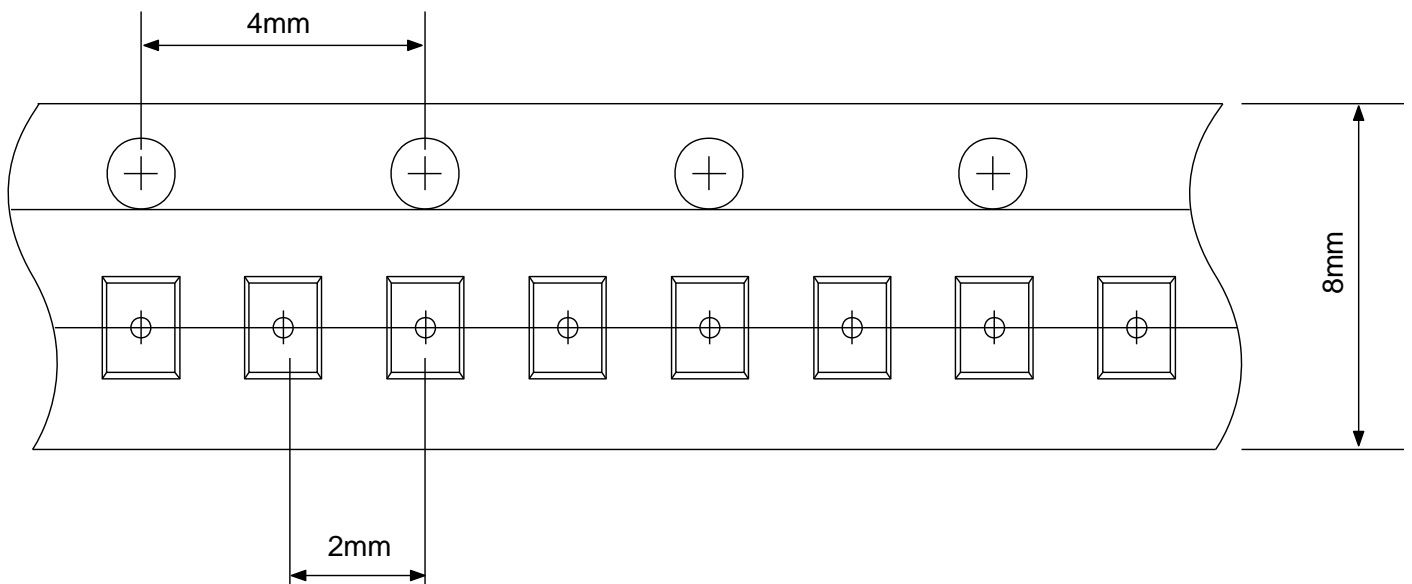
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.


TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions





User Direction of Feed

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